

General Description

The Sanrise SRC65R052FB is a high voltage power MOSFET, fabricated using advanced super junction technology. The resulting device has extremely low on resistance, low gate charge and fast switching time, making it especially suitable for applications which require superior power density and outstanding efficiency.

The SRC65R052FB break down voltage is 650V and it has a high rugged avalanche characteristic. The SRC65R052FB is available in TO-247 package.

Features

- Ultra Low $R_{DS(ON)} = 52m\Omega @ V_{GS} = 10V$.
- Ultra Low Gate Charge, $Q_g = 75.6nC$ typ.
- $V_{ds}@T_{jmax} = 700v$
- Ultra-fast body diode
- Robust design with better EAS performance

Application

- EV Charger
- Server / Telecom

Symbol

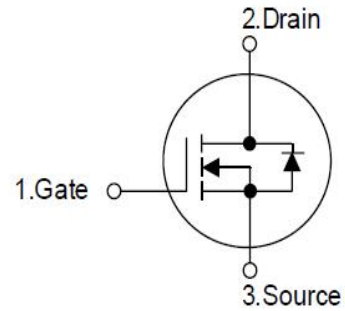
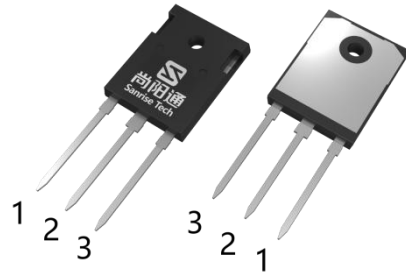


Figure 1 Symbol of SRC65R052FB

Package Type



TO-247

Figure 2 Package Type of SRC65R052FB

Ordering Information

Circuit Type		SRC65R052FB□□-□	
Package		E: Lead Free	
T: TO-247		G: Green	
		Blank: Tube	
		TR: Tape & Reel	

Package	Part Number	Marking ID	Packing Type
TO-247	SRC65R052FBT-G	SRC65R052FBTG	Tube

Absolute Maximum Ratings

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage (static)		V_{GSS}	±20	V
Gate-Source Voltage (dynamic), AC ($f > 1$ Hz)		V_{GSS}	±30	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	64.8	A
	$T_C = 125^\circ\text{C}$		29.0	
Pulsed Drain Current (Note 2)		I_{DM}	194.4	A
Avalanche Energy, Single Pulse (Note 3)		E_{AS}	700	mJ
Avalanche Energy, Repetitive (Note 2)		E_{AR}	0.2	mJ
Avalanche Current, Repetitive (Note 2)		I_{AR}	5.0	A
Continuous Diode Forward Current		I_S	64.8	A
Diode Pulse Current		$I_{S,PULSE}$	194.4	A
MOSFET dv/dt Ruggedness, $V_{DS} \leq 480\text{V}$		dv/dt	80	V/ns
Reverse Diode dv/dt , $V_{DS} \leq 480\text{V}$, $I_{SD} \leq I_D$		dv/dt	50	V/ns
Operating Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 to 150	$^\circ\text{C}$
Lead Temperature (Soldering, 10 sec)		T_{LEAD}	260	$^\circ\text{C}$

Note:

1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. $I_{AS} = 5.0\text{A}$, $V_{DD} = 60\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

Thermal Resistance

Parameter (TO247-package)	Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	-		0.31	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	-		62	

Electrical Characteristics

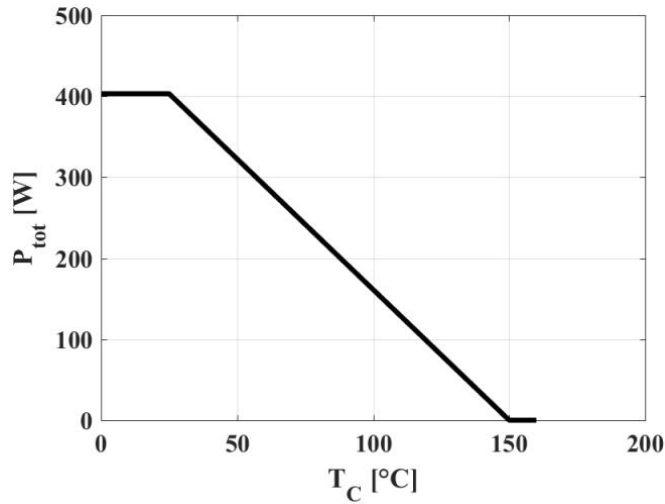
$T_J = 25^\circ\text{C}$, unless otherwise specified.

Parameter		Symbol	Test Conditions	Min	Typ	Max	Unit
Statistic Characteristics							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D =250uA	650			V
Zero Gate Voltage Drain Current		I _{DSS}	V _{DS} =650V, V _{GS} =0V			10	uA
Gate-Body Leakage Current	Forward	I _{GSSF}	V _{GS} =20V, V _{DS} =0V			100	nA
	Reverse	I _{GSSR}	V _{GS} =-20V, V _{DS} =0V			-100	
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =1.6mA	3.0	4.0	5.0	V
Static Drain-Source On-Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =38A		38	52	mΩ
Gate Resistance		R _G	f=1MHz, Open Drain		1.3		Ω
Dynamic Characteristics							
Input Capacitance		C _{ISS}	V _{DS} =50V, V _{GS} =0V, f=1MHz		5.1		nF
Output Capacitance		C _{OSS}			239		pF
Reverse Transfer Capacitance		C _{RSS}			1.7		
Effective output capacitance, energy related ^{NOTE5}		C _{O(er)}	V _{GS} =0V, V _{DS} =0...400V		135.1		pF
Effective output capacitance, time related ^{NOTE6}		C _{O(tr)}			822.4		
Turn-on Delay Time		t _{d(on)}	V _{DD} =400V, I _D =34A R _G =3.3Ω, V _{GS} =10V		15		ns
Rise Time		t _r			6.0		
Turn-off Delay Time		t _{d(off)}			62		
Fall Time		t _f			4.2		
Gate Charge Characteristics							
Gate to Source Charge		Q _{gs}	V _{DD} =480V, I _D =34A V _{GS} =0 to 10V		35.4		nC
Gate to Drain Charge		Q _{gd}			20.5		
Gate Charge Total		Q _g			75.6		
Gate Plateau Voltage		V _{plateau}			6.5		V
Reverse Diode Characteristics							
Drain-Source Diode Forward Voltage		V _{SD}	V _{GS} =0V, I _{SD} =34A		0.92	1.1	V
Reverse Recovery Time		t _{rr}	V _R =100V, I _F =34A dI _F /dt=100A/us		149		ns
Reverse Recovery Charge		Q _{rr}			0.96		uC
Peak Reverse Recovery Current		I _{rrm}			12.9		A

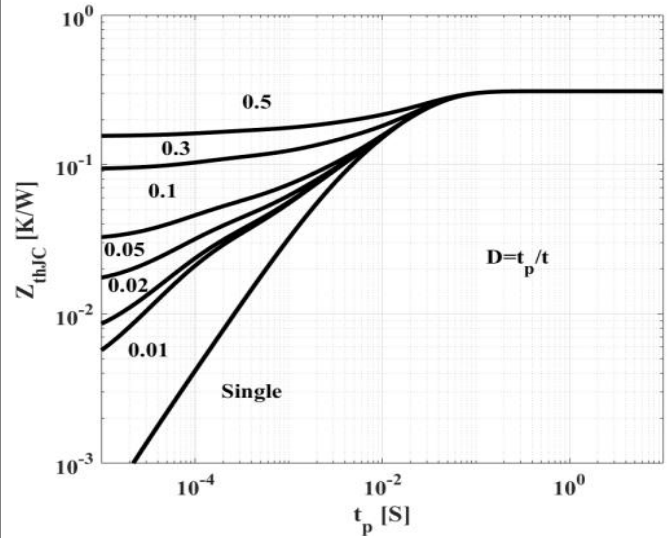
Note:

5. $C_{O(er)}$ is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 to 400V

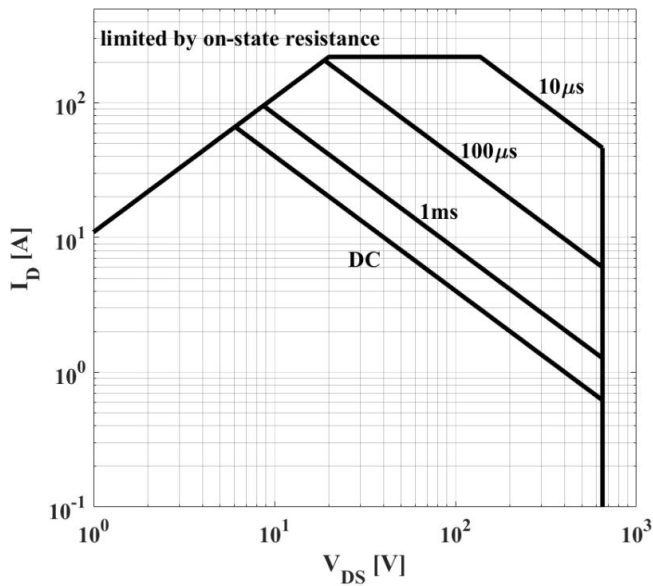
6. $C_{O(tr)}$ is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 400 V

Typical Performance Characteristics
Figure 3: Power Dissipation


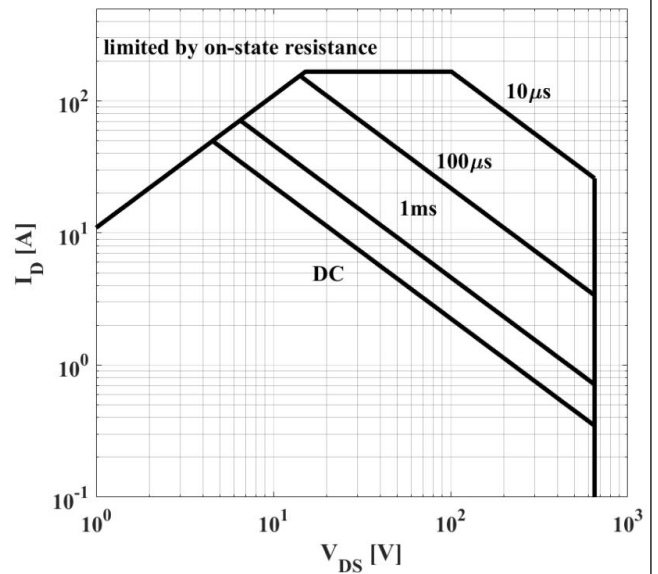
$$P_{tot} = f(T_c)$$

Figure 4: Max. Transient Thermal Impedance


$$Z_{thJC} = f(t_p); \text{ parameter: } D = t_p/T$$

Figure 5: Safe Operating Area


$$I_D = f(V_{DS}); T_c = 25^\circ\text{C}; V_{GS} > 7\text{V}; \text{ parameter } t_p$$

Figure 6: Safe Operating Area


$$I_D = f(V_{DS}); T_c = 80^\circ\text{C}; V_{GS} > 7\text{V}; \text{ parameter } t_p$$

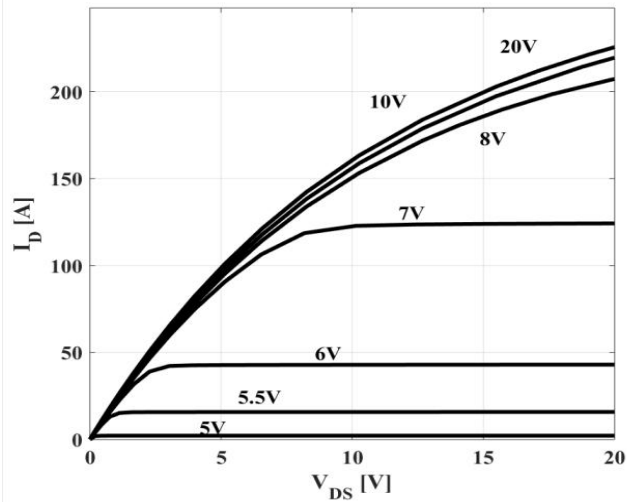
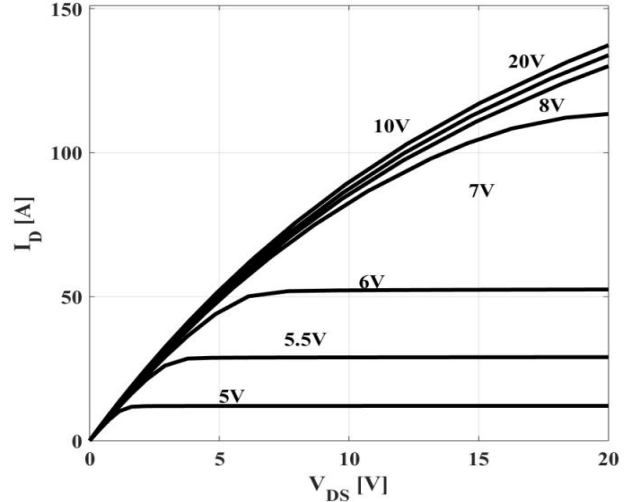
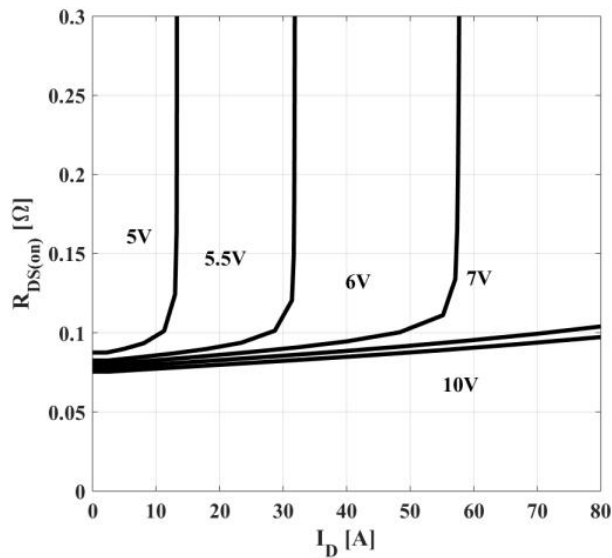
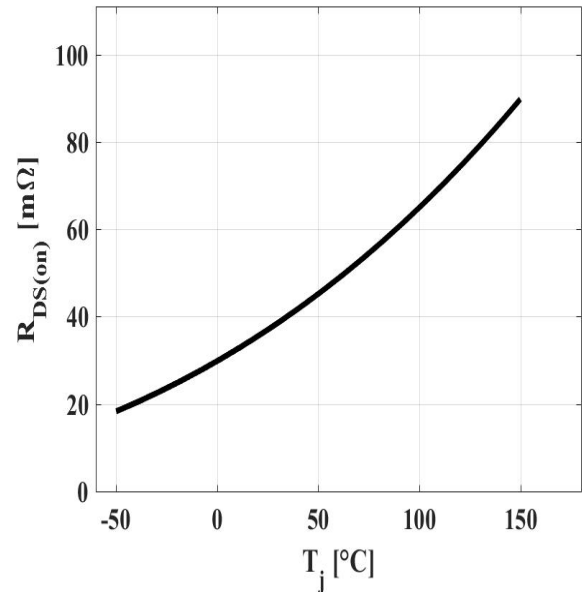
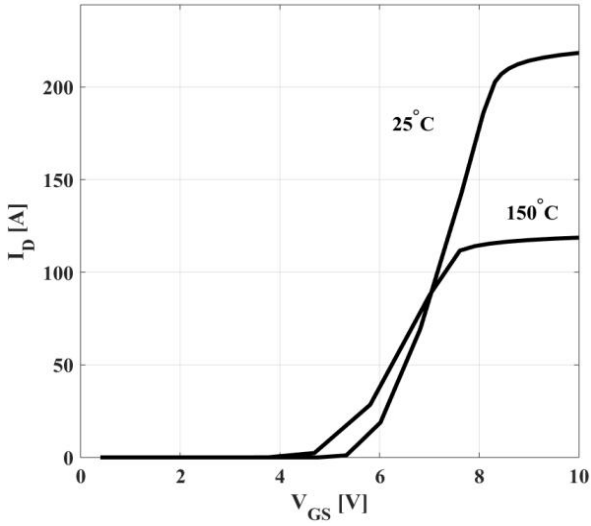
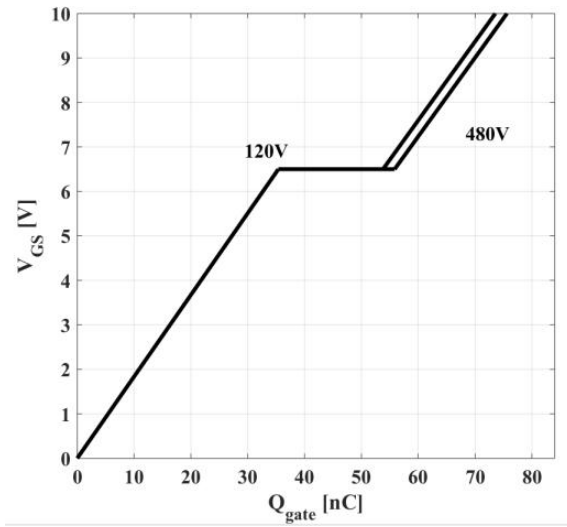
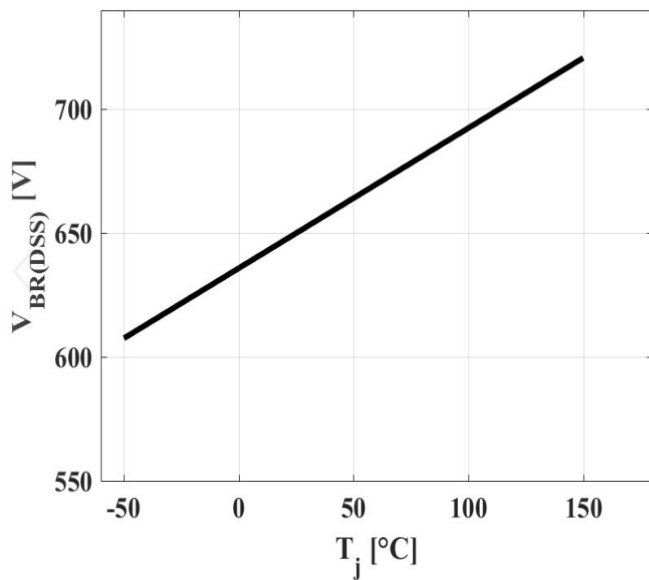
52mΩ 650V, Super Junction N-Channel Power MOSFET
SRC65R052FB
Figure 7: Typ. Output Characteristics

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}; \text{parameter: } V_{GS}$
Figure 8: Typ. Output Characteristics

 $I_D = f(V_{DS}); T_j = 125^\circ\text{C}; \text{parameter: } V_{GS}$
Figure 9: Typ. Drain-Source On-State Resistance

 $R_{DS(ON)} = f(I_D); T_j = 125^\circ\text{C}; \text{parameter: } V_{GS}$
Figure 10: Typ. Drain-Source On-State Resistance

 $R_{DS(ON)} = f(T_j); I_D = 38\text{A}; V_{GS} = 10\text{V}$

Figure 11: Typ. Transfer Characteristics


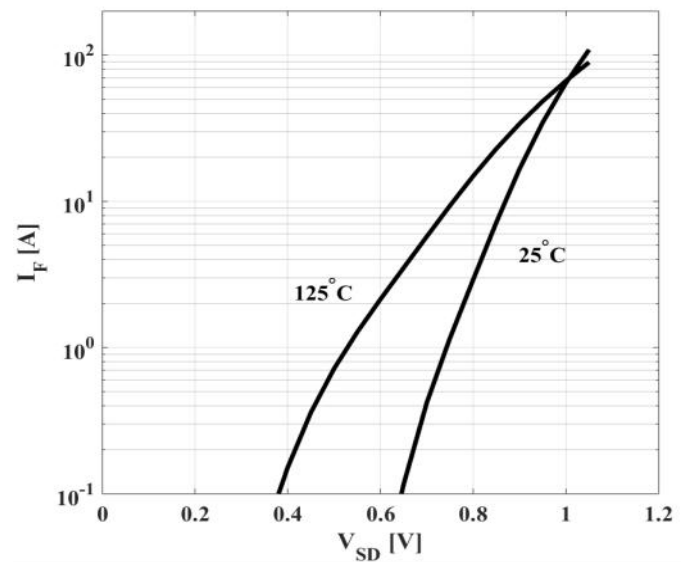
$$I_D = f(V_{GS}); V_{DS} = 20V$$

Figure 12: Typ. Gate Charge


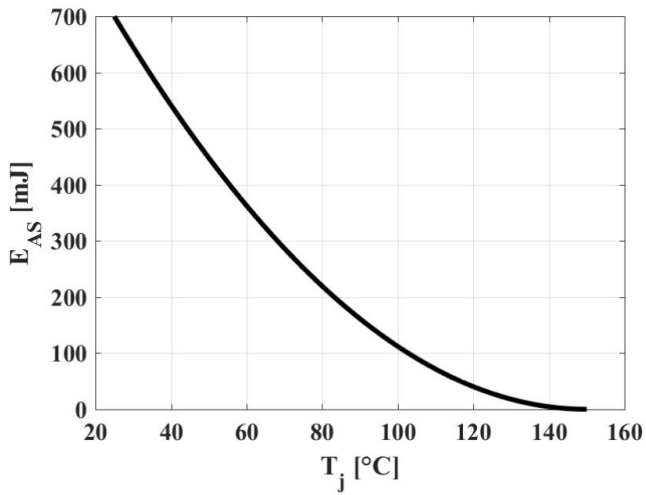
$$V_{GS} = f(Q_{gate}), I_D = 34A \text{ pulsed}$$

Figure 13: Drain-Source Breakdown Voltage


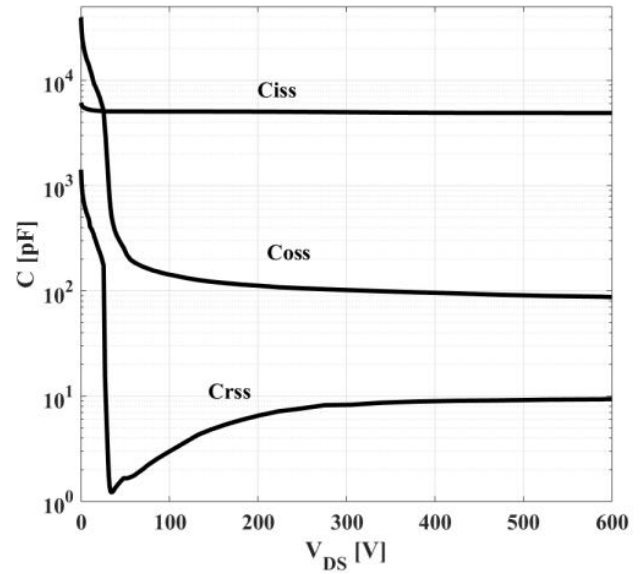
$$V_{BR(DSS)} = f(T_j); I_D = 1mA$$

Figure 14: Forward Characteristics of Reverse Diode


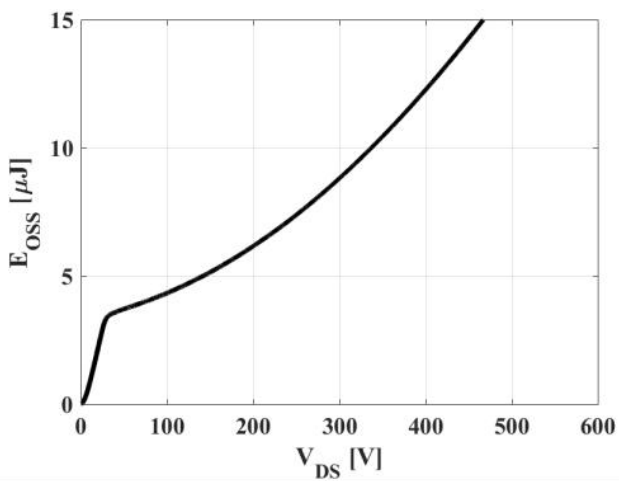
$$I_F = f(V_{SD}); \text{parameter: } T_j$$

Figure 15: Avalanche Energy


$$E_{AS}=f(T_j); I_D=5.0A; V_{DD}=60V$$

Figure 16: Typ. Capacitances


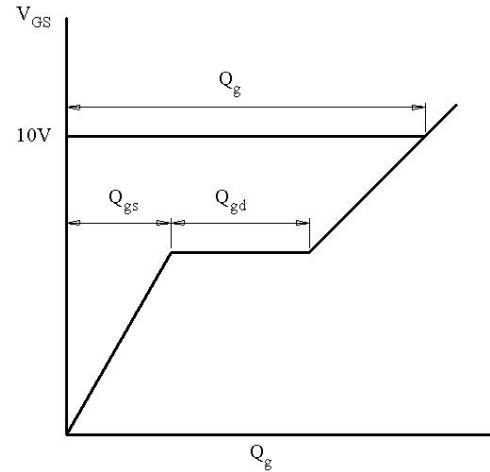
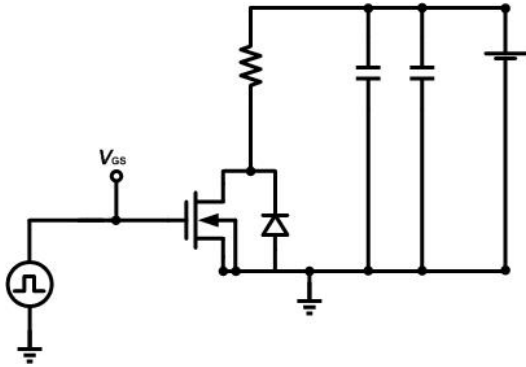
$$C=f(V_{DS}); V_{GS}=0; f=1MHz$$

Figure 17: Coss Stored Energy


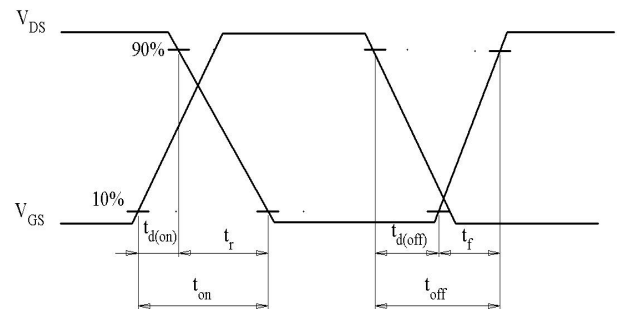
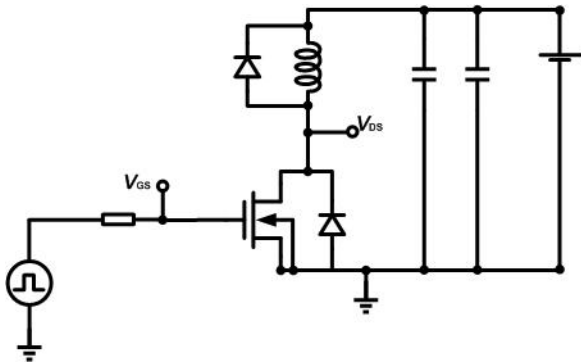
$$E_{OSS}=f(V_{DS})$$

Test Circuits

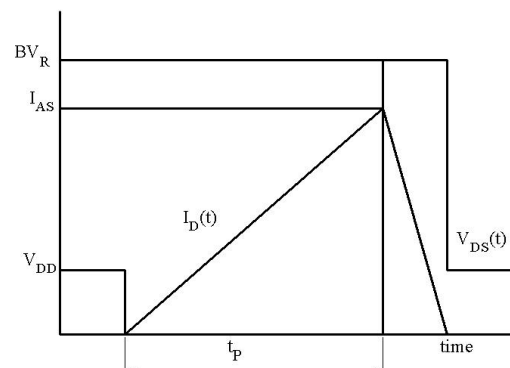
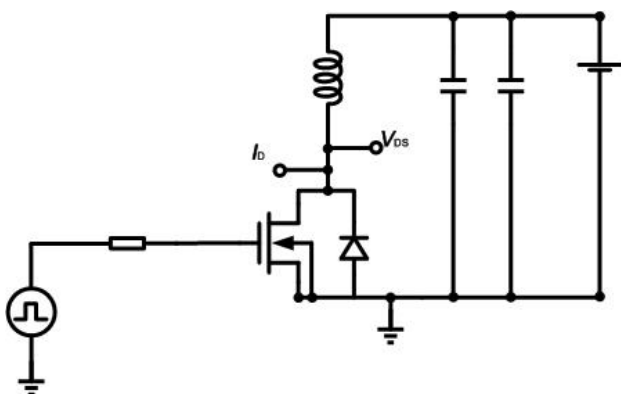
1. Gate Charge Test Circuit & Waveform



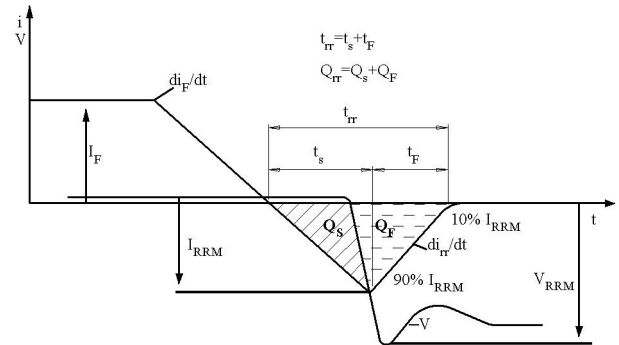
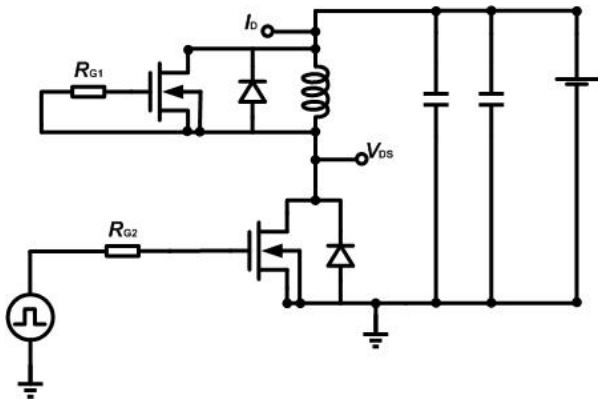
2. Switch Time Test Circuit

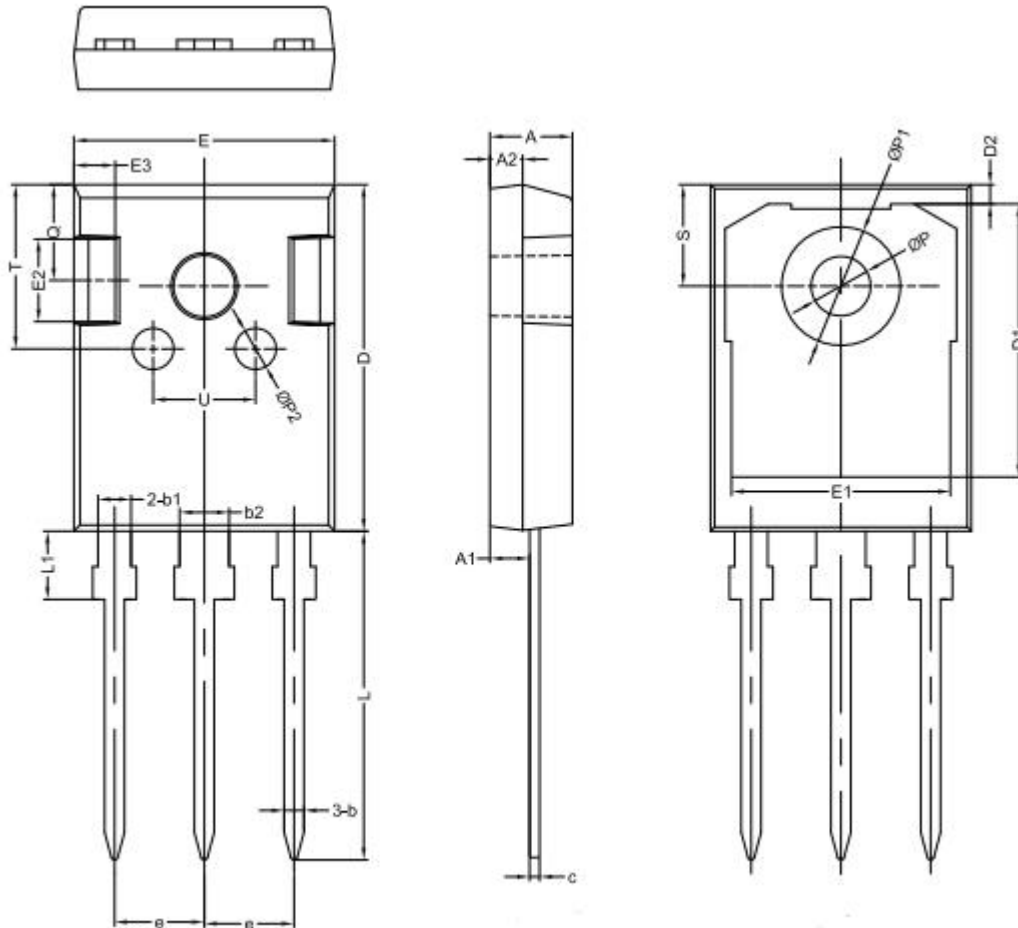


3. Unclaimed Inductive Switching Test Circuit & Waveforms

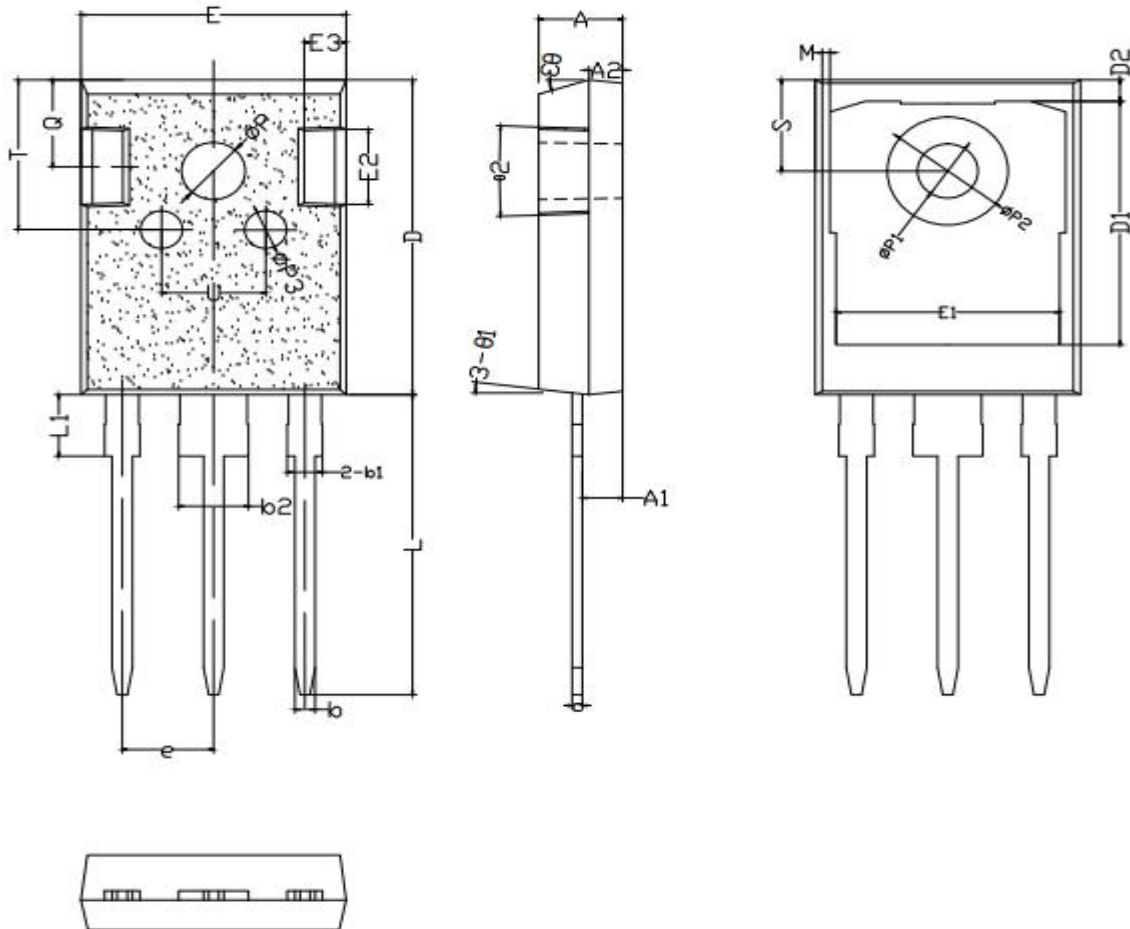


4. Test Circuit and Waveform for Diode Characteristics

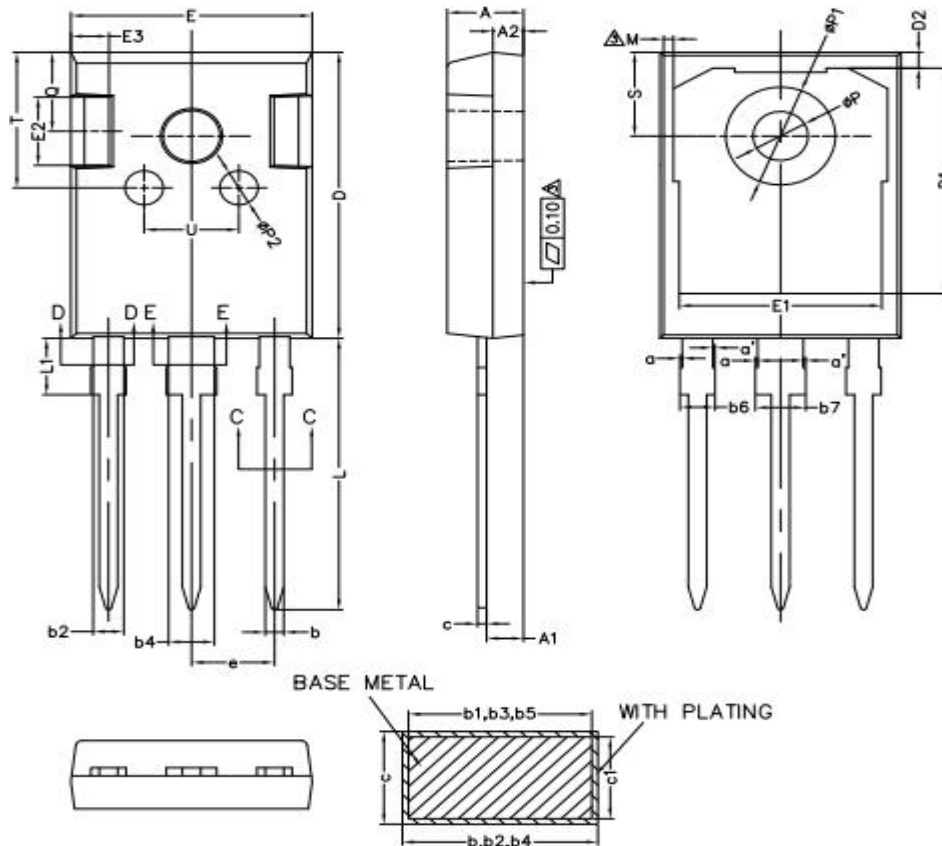


Mechanical Dimensions
TO-247(Package 1)
Unit: mm


Symbol	Dimensions(mm)			Symbol	Dimensions(mm)		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.80	5.00	5.20	E1	-	13.30	-
A1	2.21	2.41	2.61	E2	-	5.00	-
A2	1.90	2.00	2.10	E3	-	2.50	-
b	1.10	1.20	1.35	L	19.42	19.92	20.42
b1	-	2.00	-	L1	-	4.13	-
b2	-	3.00	-	P	3.50	3.60	3.70
c	0.55	0.60	0.75	P1	-	7.19	-
D	20.80	21.00	21.20	P2	-	2.50	-
D1	-	16.55	-	Q	-	5.80	-
D2	-	1.20	-	S	6.05	6.15	6.25
E	15.60	15.80	16.0	T	-	10.00	-
U	-	6.20	-				

Mechanical Dimensions
TO-247(Package 2)
Unit: mm


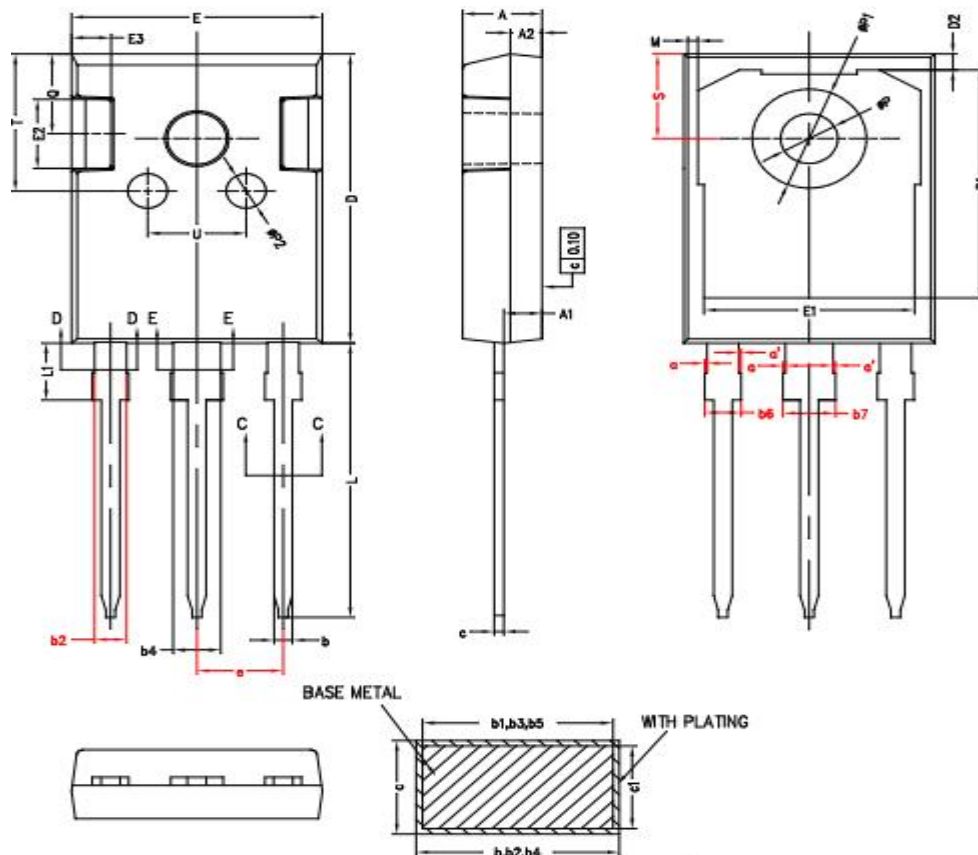
Symbol	Dimensions(mm)			Symbol	Dimensions(mm)		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.90	5.00	5.10	E1	13.10	13.25	13.40
A1	2.31	2.41	2.51	E2	4.85	4.95	5.10
A2	1.90	2.00	2.10	E3	2.40	2.50	2.60
b	1.15	1.20	1.25	L	19.80	19.98	20.15
b1	1.95	2.10	2.25	L1	-	-	4.30
b2	2.95	3.10	3.25	ΦP	3.60	3.70	3.80
c	0.55	0.60	0.65	ΦP1	3.40	3.50	3.60
D	20.90	21.00	21.10	ΦP2	6.90	7.10	7.30
D1	16.35	16.55	16.75	Q	5.60	5.80	6.00
D2	1.05	1.20	1.35	S	6.05	6.15	6.25
E	15.70	15.80	15.90	T	9.80	10.00	10.20
U	6.00	6.20	6.40	e	5.40	5.44	5.48
θ1	5°	7°	9°	ΦP3	2.40	2.50	2.60
θ2	1°	3°	5°	θ3	13°	15°	17°

Mechanical Dimensions
TO-247(Package 3)
Unit: mm


Symbol	Dimensions(mm)			Symbol	Dimensions(mm)		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.90	5.00	5.10	c1	0.58	0.60	0.62
A1	2.31	2.41	2.51	D	20.90	21.00	21.10
A2	1.90	2.00	2.10	D1	16.25	16.55	16.85
b	1.16	-	1.26	D2	1.05	1.20	1.35
b1	1.15	1.20	1.22	E	15.70	15.80	15.90
b2	1.96	-	2.06	E1	13.10	13.30	13.50
b3	1.95	2.00	2.02	E2	4.90	5.00	5.10
b4	2.96	-	3.06	E3	2.40	2.50	2.60
b5	2.95	3.00	3.02	e	5.34	5.44	5.54
b6	-	-	2.25	L	19.80	19.92	20.10
b7	-	-	3.25	L1	3.95	4.13	4.30
c	0.59	-	0.66	M	0.35	-	0.95
P	3.50	3.60	3.70	P1	7.00	-	7.40
P2	2.40	2.50	2.60	Q	5.60	-	6.00
S	6.05	6.15	6.25	T	9.80	-	10.20
U	6.00	-	6.40	a	0	-	0.15
a'	0	-	0.15				

Mechanical Dimensions
TO-247(Package 4)

Unit: mm



Symbol	Dimensions(mm)			Symbol	Dimensions(mm)		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.90	5.00	5.10	E2	4.90	5.00	5.10
A1	2.31	2.41	2.51	E3	2.40	2.50	2.60
A2	1.90	2.00	2.10	e	5.34	5.44	5.54
b	1.12	-	1.22	L	19.80	19.92	20.10
b1	1.11	1.16	1.18	L1	3.95	4.13	4.30
b2	1.96	-	2.06	P	3.50	3.60	3.70
c	0.59	-	0.66	P1	7.00	-	7.40
D	20.90	21.00	21.10	P2	2.40	2.50	2.60
D1	16.25	16.55	16.85	Q	5.60	-	6.00
D2	1.05	1.20	1.35	S	6.05	6.15	6.25
E	15.70	15.80	15.90	T	9.80	-	10.20
E1	13.10	13.30	13.50	U	6.00	-	6.40
b3	1.95	2.00	2.02	b6	-	-	2.25
b4	2.96	-	3.06	b7	-	-	3.25
b5	2.95	3.00	3.02	c1	0.58	0.60	0.62
M	0.35	-	0.95	a	0	-	0.15
a'	0	-	0.15				



Shenzhen Sanrise Technology Co., LTD

<http://www.sanrise-tech.com>

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Main Site:

- Headquarter

Shenzhen Sanrise Technology Co., LTD.

A1206, Skyworth building, No. 008, gaoxinnan 1st Road,
Gaoxin District, Yuehai street,, Nanshan District, ShenZhen,
P.R.China

Tel: +86-755-22953335

Fax: +86-755-22916878

- Shanghai Office

Shenzhen Sanrise Technology Co., LTD

Rm.702, Building A, No. 666, Zhangheng Road,
Zhangjiang Hi-Tech Park, Shanghai, P.R.China

Tel: +86-21-68825918